

## IN THE CLAIMS

Please make the following amendments to the claims:

1. (Currently Amended) A power-up circuit of a semiconductor memory device, comprising:

a power supply voltage level follower unit for providing a bias voltage which is linearly varied according to variation of a power supply voltage;

a power supply voltage detection unit for detecting whether a voltage level of the power supply voltage reaches a predetermined critical voltage level in response to the bias voltage to thereby generate a detection signal; and

a reset prevention unit, including two pull-up devices and a pull-down device controlled by the detection signal and a delayed detection signal, for generating a power-up signal ~~by performing a pull-down operation controlled by the detection signal and a delayed detection signal~~ to thereby prevent a logic level of the power-up signal from transitioning during a power drop of the power supply voltage having a duration less than or equal to a predetermined period, wherein the delayed detection signal is generated by delaying the detection signal.

2. (Previously Presented) The power-up circuit as recited in claim 1, further comprising a buffer unit for outputting the power-up signal by buffering the detection signal.

3. (Previously Presented) The power-up circuit as recited in claim 1, wherein the reset prevention unit includes:

a first pull-up means and a first pull-down means controlled by the detection signal; and

a response delaying means for delaying a pull-up operation of the first pull-up means according to a transition of the detection signal.

4. (Previously Presented) The power-up circuit as recited in claim 3, wherein the response delay means includes:
  - a delay unit for delaying the detection signal by a predetermined time; and
  - a second pull-up means connected between the first pull-up means and a power supply voltage, and controlled by an output signal of the delay unit.
5. (Original) The power-up circuit as recited in claim 4, wherein the predetermined time for delaying the output signal of the power supply voltage detection unit in the delay unit is longer than a time that the detection signal is maintained in a logic low level due to the power drop.
6. (Original) The power-up circuit as recited in claim 4, wherein the reset prevention unit further includes an inverter connected to the first pull-up means and the first pull-down means.
7. (Previously Presented) The power-up circuit as recited in claim 4, wherein each of the first and second pull-up means is a PMOS transistor, and the pull-down means is an NMOS transistor.
8. (Previously Presented) The power-up circuit as recited in claim 4, wherein the power supply voltage level follower unit is provided between the power supply voltage and a ground voltage, and includes a first and a second load elements configured as a voltage divider.
9. (Previously Presented) The power-up circuit as recited in claim 4, wherein the power supply voltage detection unit includes:
  - a load element connected between the power supply voltage and a first node;
  - an NMOS transistor which is connected between a ground voltage and the first node and whose gate receives the bias voltage; and
  - an inverter, which is connected to the first node, for outputting the detection signal.

10. (Original) The power-up circuit as recited in claim 9, wherein the load element is a PMOS transistor which is connected between the power supply voltage and the first node, and whose gate is connected to the ground voltage.

11. (Original) The power-up circuit as recited in claim 2, wherein the buffer unit includes an inverter chain receiving an output signal of the reset prevention unit.

12. (Previously Presented) A power initialization circuit for a semiconductor memory device, comprising:

- a power supply voltage level follower unit to provide a bias voltage which varies linearly with a power supply voltage;

- a power supply voltage detection unit to detect when a level of the power supply voltage reaches a predetermined level; and

- a reset prevention unit to generate a power-up signal, the reset prevention unit including two pull-up devices in series with a pull-down device, the pull-down device and one pull-up device controlled by a signal from the power supply voltage detection unit and one pull-up device controlled by a delayed version of the signal from the power supply voltage detection unit.